

-20V P-Channel Enhancement Mode MOSFET

Description

The SX16P02S uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = -20V I_D =-16A

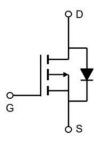
 $R_{DS(ON)}$ < 20m Ω @ Vgs=-4.5V

Application

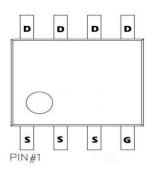
Battery protection

Load switch

Uninterruptible power supply







Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-20	V
VGS	Gate-Source Voltage	±12	V
lo@Tc=25℃	Continuous Drain Current, V _{GS} @ -4.5V ¹	-16	А
lo@Tc=70°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-8	А
IDM	Pulsed Drain Current ²	-48	А
P □@ Tc= 25 °C	Total Power Dissipation ³	2.5	W
P o@T c=70°C	Total Power Dissipation ³	1.6	W
TSTG	Storage Temperature Range	-55 to 150	$^{\circ}$
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$
R₀JA	Thermal Resistance Junction-Ambient ¹	85	°C/W
R₀JC	Thermal Resistance Junction-Case ¹	24	°C/W





Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , Ip=-250uA	-20	-24		V
△BVDSS/△T J	BVpss Temperature Coefficient	Reference to 25°C , Ib=-1mA		-0.012		V/℃
RDS(ON)	Static Drain-Source On-Resistance ²	Vgs=-4.5V , ID=-20A		14	20	
RDS(ON)	Static Drain-Source On-Resistance ²	Vgs=-2.5V , ID=-10A		22	28	mΩ
VGS(th)	Gate Threshold Voltage	\/ \/ L 0504	-0.5	-0.6	-1.2	V
△VGS(th)	V _{GS(th)} Temperature Coefficient	Vgs=Vds , ld =-250uA		2.94		mV/℃
IDSS	Drain-Source Leakage Current	V _{DS} =-20V , V _{GS} =0V , T _J =25°C			1	uA
IGSS	Gate-Source Leakage Current	Vgs=±12V , Vps=0V			±100	nA
Qg	Total Gate Charge (-4.5V)			15.3		
Qgs	Gate-Source Charge	VDS=-10V , VGS=-4.5V , ID=-6A		2.2		nC
Qgd	Gate-Drain Charge			4.4		
Td(on)	Turn-On Delay Time			10		
Tr	Rise Time	V _{DD} =-10V , V _{GS} =-4.5V ,		31		
Td(off)	Turn-Off Delay Time	R _G =3.3Ω, I _D =-10A		28		ns
Tf	Fall Time			8		
Ciss	Input Capacitance			2000		
Coss	Output Capacitance	V _{DS} =-10V , V _{GS} =0V , f=1MHz		242		pF
Crss	Reverse Transfer Capacitance			231		
IS	Continuous Source Current ^{1,4}				-20	Α
ISM	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			-48	Α
VSD	Diode Forward Voltage ²	Vgs=0V , Is=-1A , Tյ=25℃			-1.2	V

Note:

- 1 、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2 . The data tested by pulsed , pulse width $\,\, \leqq \, 300 us$, duty cycle $\,\, \leqq \, 2\%$
- $3\,{}_{\smallsetminus}$ The power dissipation is limited by $150\,{}^\circ\!\mathrm{C}\textsc{junction}$ temperature
- 4 . The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

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Typical Characteristics

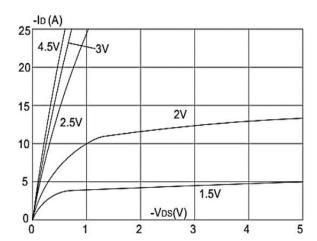


Figure1: Output Characteristics

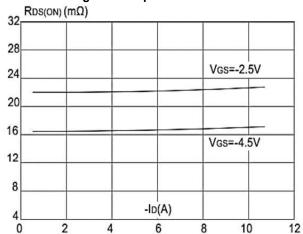


Figure 3:On-resistance vs. Drain Current

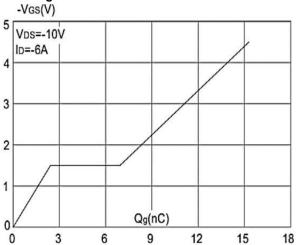


Figure 5: Gate Charge Characteristics

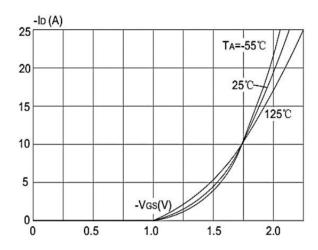


Figure 2: Typical Transfer Characteristics

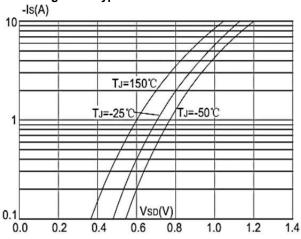


Figure 4: Body Diode Characteristics

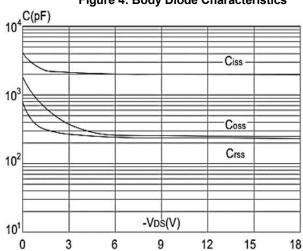


Figure 6: Capacitance Characteristics





Typical Characteristics

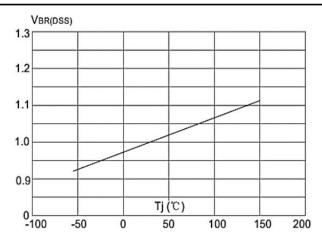


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

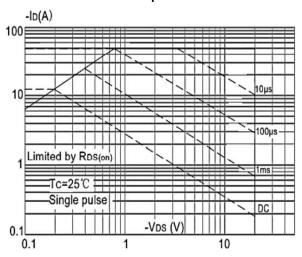


Figure 9: Maximum Safe Operating Area

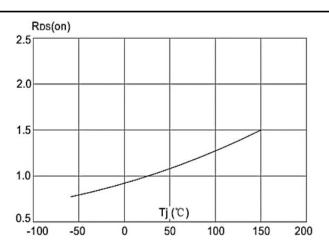


Figure 8: Normalized on Resistance vs.

Junction Temperature

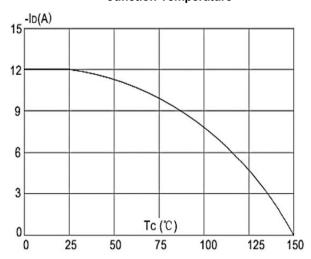


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

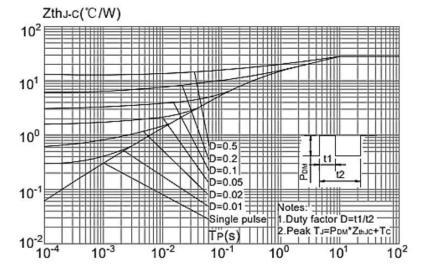


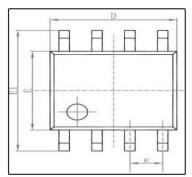
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien

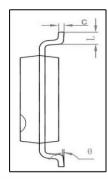
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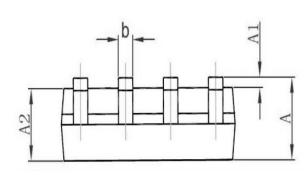
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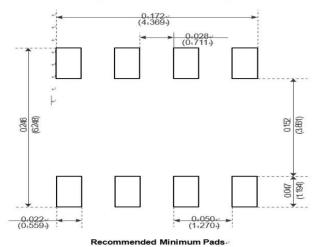
Package Mechanical Data-SOP-8







Symbol	Dimensions In	n Millimeters	Dimensions	In Inches
	Min	Max	Min	Max
Α	1. 350	1. 750	0. 053	0.069
A1	0. 100	0. 250	0. 004	0.010
A2	1. 350	1. 550	0. 053	0.061
b	0. 330	0. 510	0. 013	0.020
С	0. 170	0. 250	0.006	0.010
D	4. 700	5. 100	0. 185	0. 200
E	3.800	4. 000	0. 150	0. 157
E1	5. 800	6. 200	0. 228	0. 244
е	1. 270	(BSC)	0. 050	(BSC)
L	0. 400	1. 270	0. 016	0.050
θ	0°	8°	0°	8°



Package Marking and Ordering Information

ackage marking and cracing information					
Product ID	Pack	Marking	Qty(PCS)		
TAPING	SOP-8		3000		

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